DOCUMENT CHANGE REQUEST

DCR number 1637 Date: 2024/03/04 Status: IMPLEMENTED	Changes required for: General Date sent: 2024/02/05	Originator: Steve Thacker Organisation: ESCC Executive Secretariat

Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH8N10		
Number:	5205/023	Issue:	9

Other documents affected:

Page:

Various; see attached spec mark-up Draft 10 for details

Paragraph:

See below

Original wording:

As per spec issue 9

Proposed wording:

Amend the maximum limit for Gate-to-Source Threshold Voltage, VGS(th), as follows:
see attached spec mark-up Draft 10A for details.

Paras. 2.4.1, 2.5, 2.6, 2.10.2:
to be 4.7V maximum (was 4.5V max.)

Para. 2.4.2:
for +125C only: to be 4.1V maximum (was 3.7V max.)

Justification:

This DCR is raised on behalf of Manufacturer STM.

STM stated: The reason is: better limit definition due to old and poor statistical data

Attachments:
escc5205023iss10_draft_a_in_review.docx
Modifications:
N/A
Approval signature:
Date signed:
2024-03-04